



## Description

The SM9435PRL uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOP-8

## General Features

$V_{DS} = -30V$   $I_D = -5.8A$

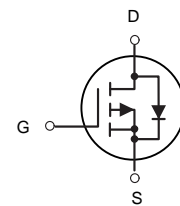
$R_{DS(ON)} < 55m\Omega$  @  $V_{GS}=10V$

## Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SM9435PRL	SOP-8	HXY MOSFET	3000

## Absolute Maximum Ratings (Tc=25°C unless otherwise noted )

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	- 30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_A=25^\circ C$	Drain Current <sup>3</sup> , $V_{GS}$ @ 10V	-5.8	A
IDM	Pulsed Drain Current <sup>1</sup>	-20	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/°C
TSTG	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$R_{thj-a}$	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	50	°C/W



**Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1	-1.6	-3	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.1A	-	43	55	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.2A	-	62	90	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-4.5A	4	7	-	S
<b>Dynamic Characteristics (Note 4)</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1.0MHz	-	520	-	PF
Output Capacitance	C <sub>oss</sub>		-	130	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	70	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, I <sub>D</sub> =-1A, V <sub>GS</sub> =-10V, R <sub>GEN</sub> =6Ω	-	7	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	13	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	14	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	9	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-5.1A, V <sub>GS</sub> =-10V	-	11	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	2.2	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-5.1A	-	-	-1.2	V

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production



### Typical Electrical and Thermal Characteristics

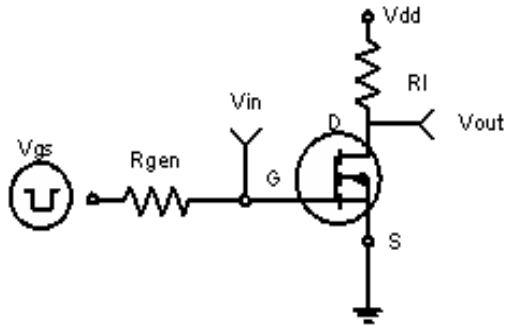


Figure 1: Switching Test Circuit

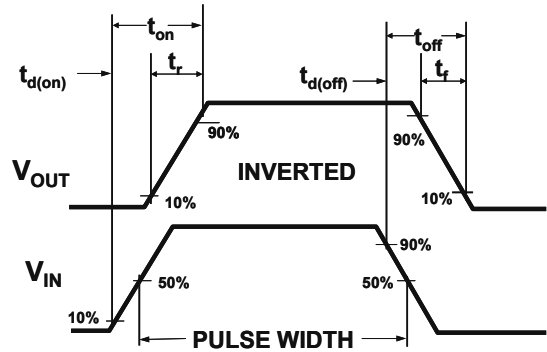


Figure 2: Switching Waveforms

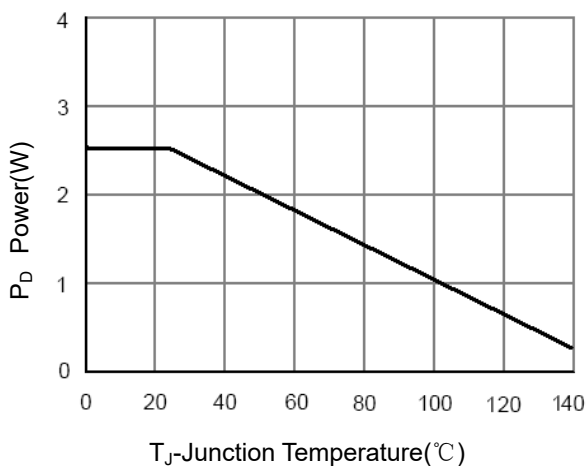


Figure 3 Power Dissipation

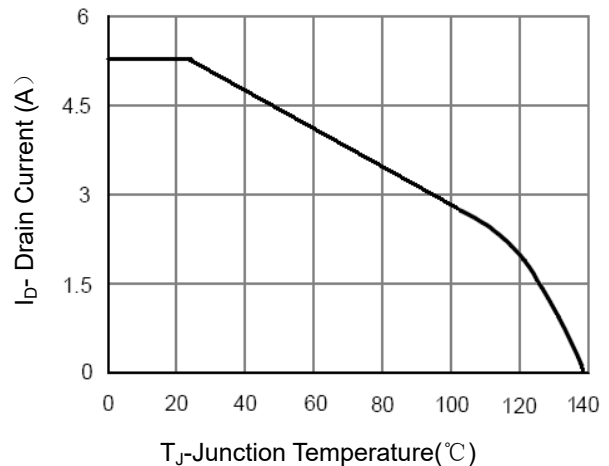


Figure 4 Drain Current

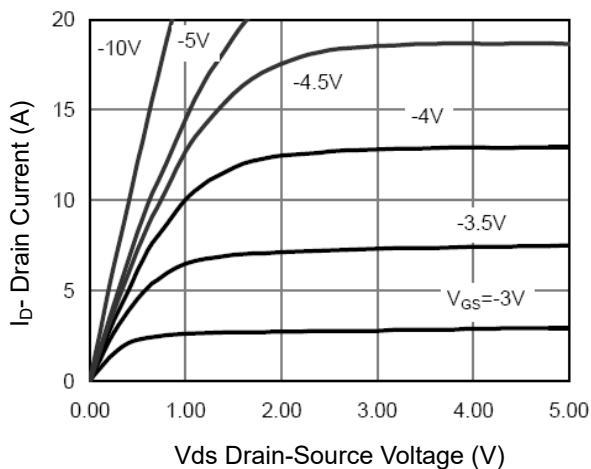


Figure 5 Output Characteristics

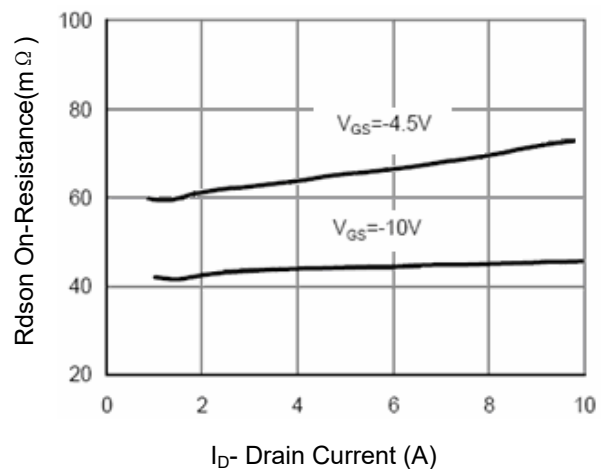
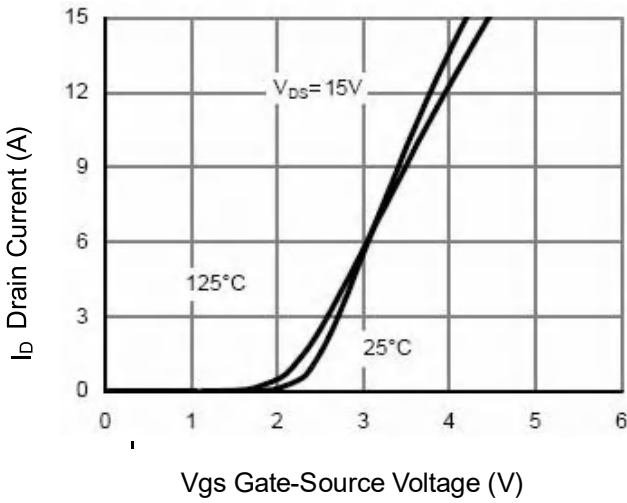


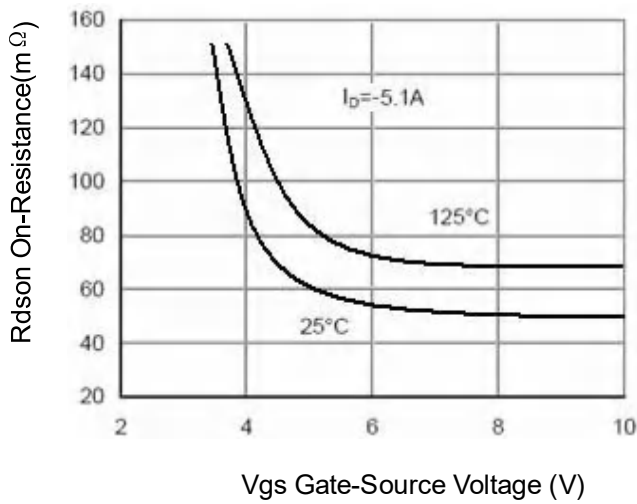
Figure 6 Drain-Source On-Resistance



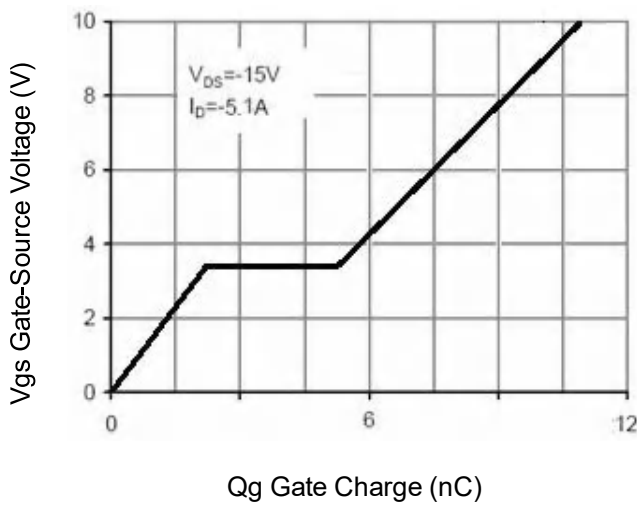
**Figure 5 Output Characteristics**



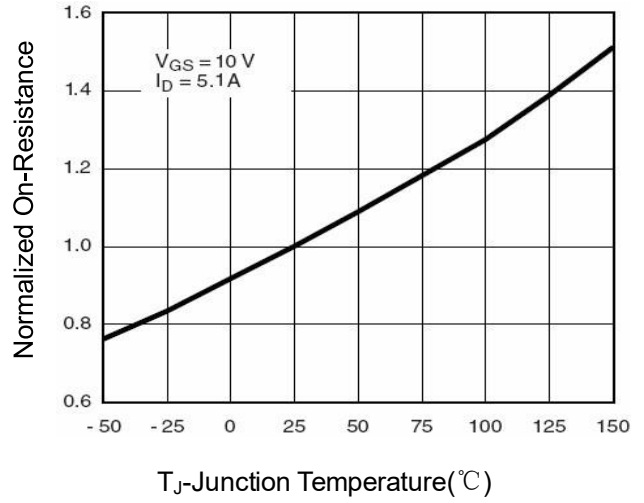
**Figure 7 Transfer Characteristics**



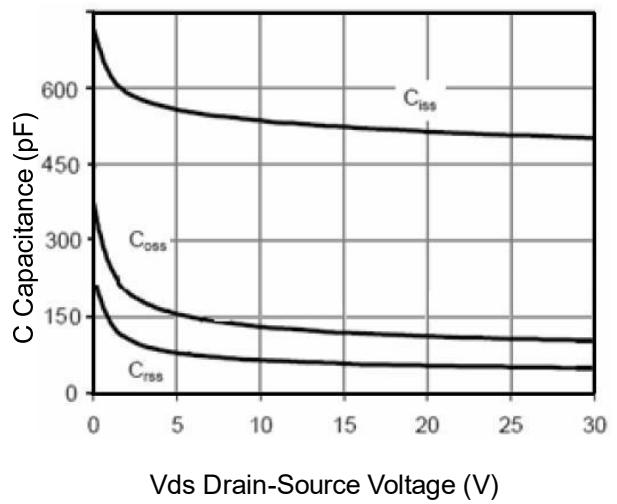
**Figure 9 Rdson vs Vgs**



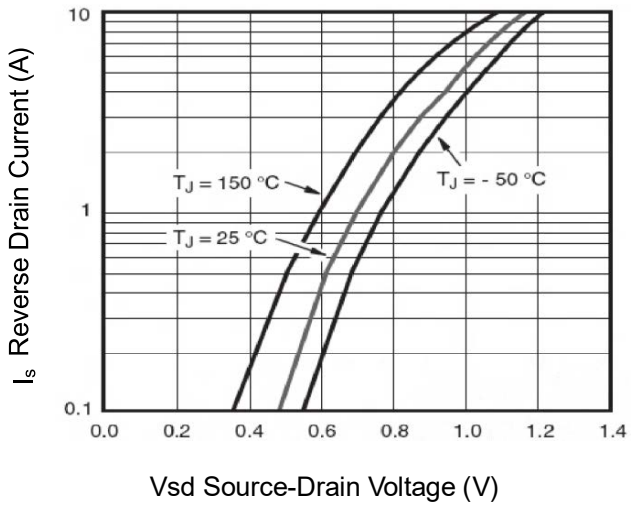
**Figure 11 Gate Charge**



**Figure 10 Capacitance vs Vds**



**Figure 12 Source- Drain Diode Forward**



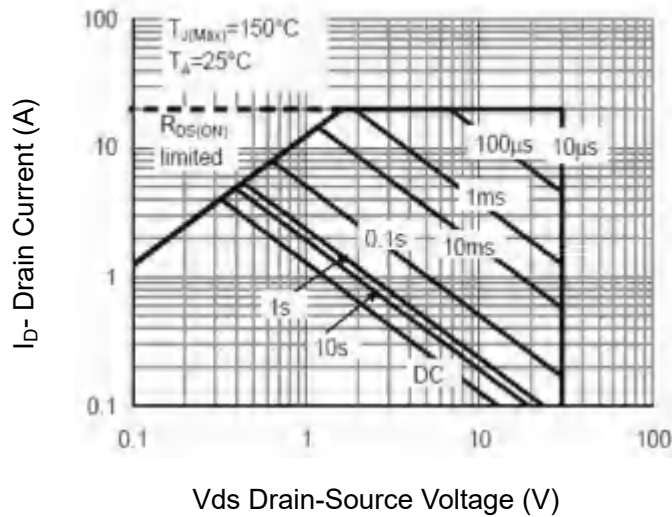


Figure 13 Safe Operation Area

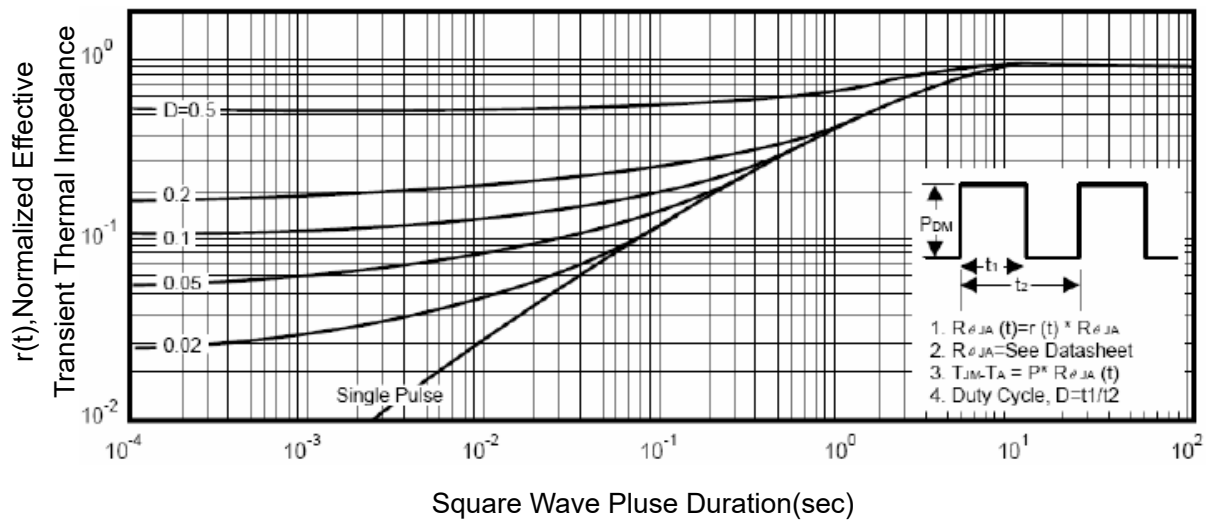
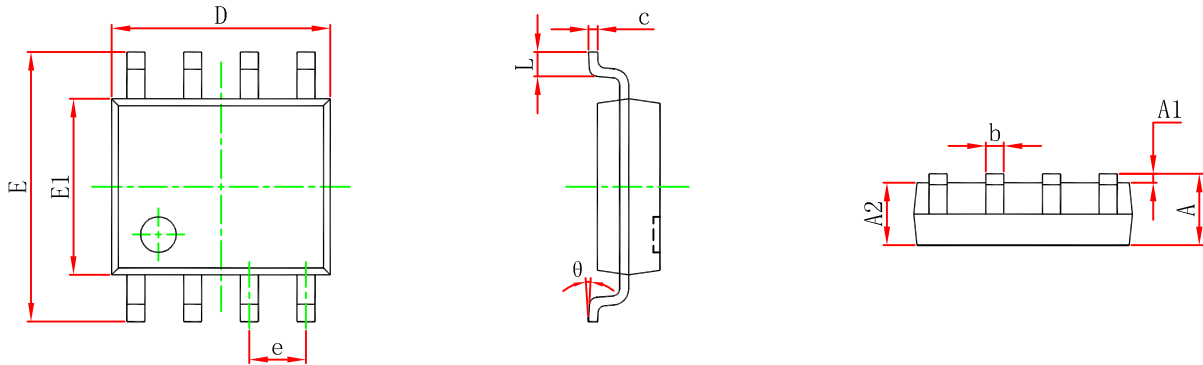


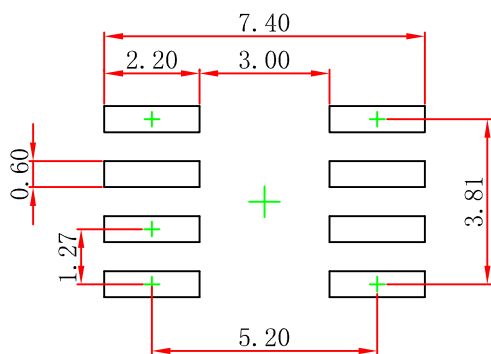
Figure 14 Normalized Maximum Transient Thermal Impedance



### SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
theta	0°	8°	0°	8°



Note:  
1. Controlling dimension: in millimeters.  
2. General tolerance:  $\pm 0.05\text{mm}$ .  
3. The pad layout is for reference purposes only.



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